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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	168
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200cq240c9

After an APEX 20KC device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Real-time changes can be made during system operation, enabling innovative reconfigurable computing applications.

APEX 20KC devices are supported by the Altera Quartus II development system, a single, integrated package that offers HDL and schematic design entry, compilation and logic synthesis, full simulation and worst-case timing analysis, SignalTap logic analysis, and device configuration. The Quartus II software runs on Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations.

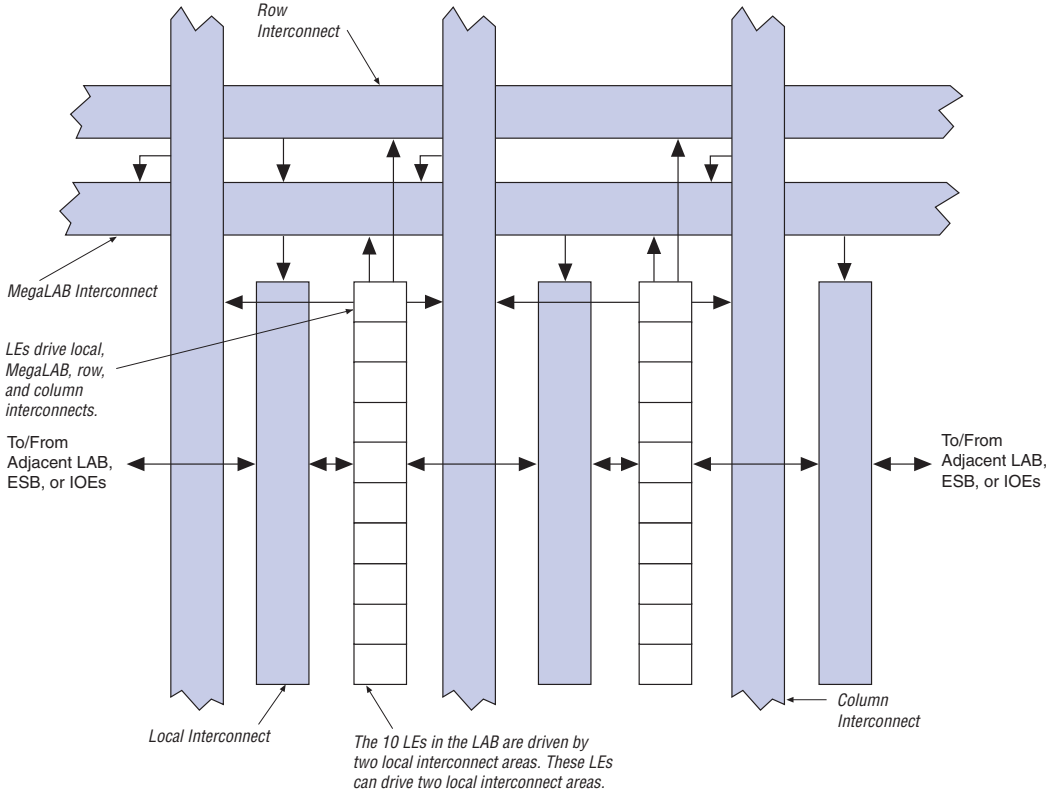
The Quartus II software provides NativeLink interfaces to other industry-standard PC- and UNIX workstation-based EDA tools. For example, designers can invoke the Quartus II software from within third-party design tools. Further, the Quartus II software contains built-in optimized synthesis libraries; synthesis tools can use these libraries to optimize designs for APEX 20KC devices. For example, the Synopsys Design Compiler library, supplied with the Quartus II development system, includes DesignWare functions optimized for the APEX 20KC architecture.

Functional Description

APEX 20KC devices incorporate LUT-based logic, product-term-based logic, and memory into one device on an all-copper technology process. Signal interconnections within APEX 20KC devices (as well as to and from device pins) are provided by the FastTrack interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KC devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

Figure 3. LAB Structure



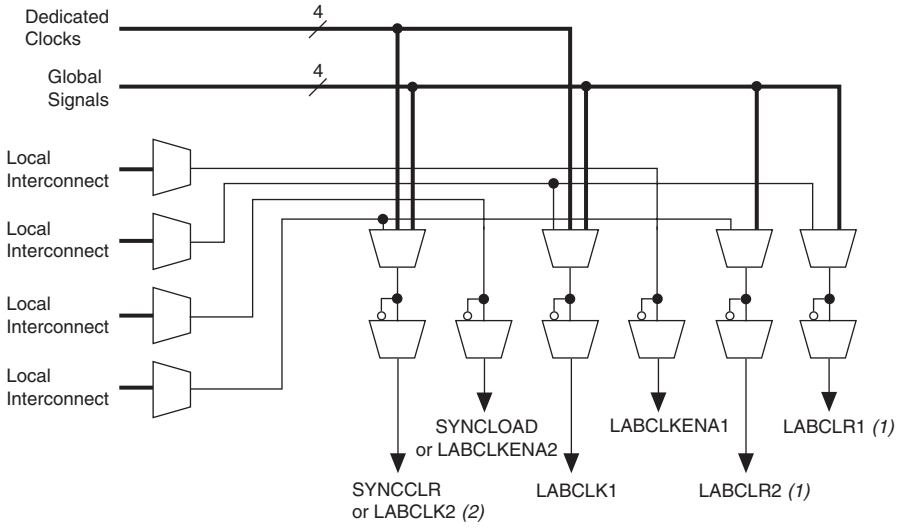
Each LAB contains dedicated logic for driving control signals to its LEs and ESBs. The control signals include clock, clock enable, asynchronous clear, asynchronous preset, asynchronous load, synchronous clear, and synchronous load signals. A maximum of six control signals can be used at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked (e.g., any LE in a particular LAB using `CLK1` will also use `CLKENA1`). LEs with the same clock but different clock enable signals either use both clock signals in one LAB or are placed into separate LABs.

If both the rising and falling edges of a clock are used in a LAB, both LAB-wide clock signals are used.

The LAB-wide control signals can be generated from the LAB local interconnect, global signals, and dedicated clock pins. The inherent low skew of the FastTrack interconnect enables it to be used for clock distribution. Figure 4 shows the LAB control signal generation circuit.

Figure 4. LAB Control Signal Generation



Notes to Figure 4:

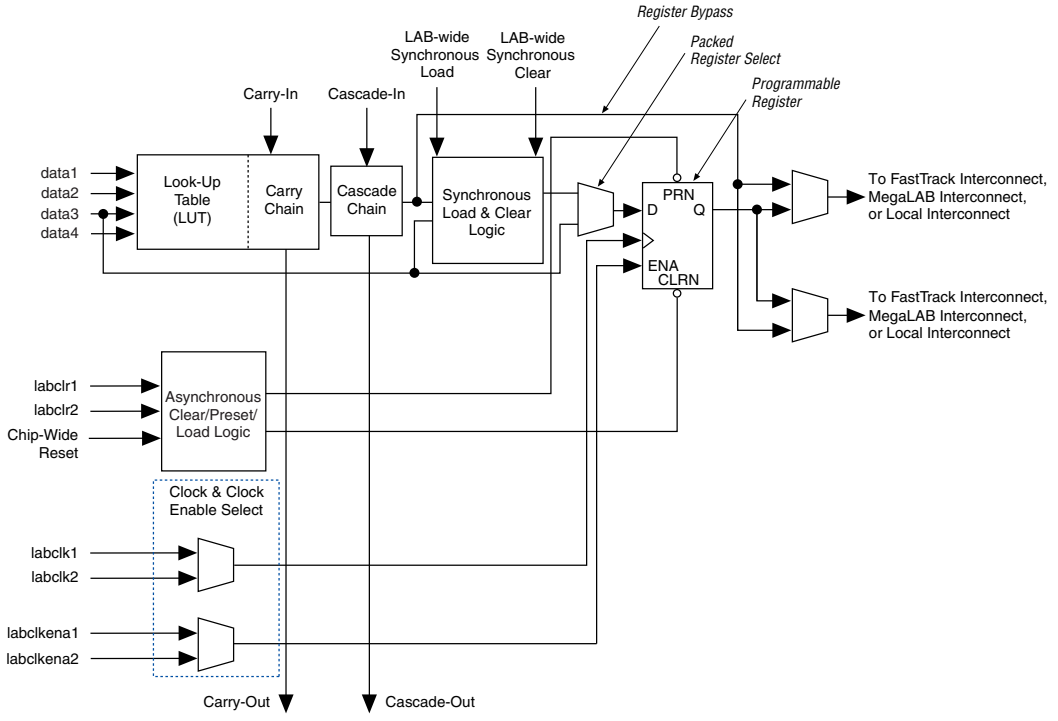
(1) The LABCLR1 and LABCLR2 signals also control asynchronous load and asynchronous preset for LEs within the LAB.

(2) The SYNCCLR signal can be generated by the local interconnect or global signals.

Logic Element

The LE, the smallest unit of logic in the APEX 20KC architecture, is compact and provides efficient logic usage. Each LE contains a four-input LUT, which is a function generator that can quickly implement any function of four variables. In addition, each LE contains a programmable register and carry and cascade chains. Each LE drives the local interconnect, MegaLAB interconnect, and FastTrack interconnect routing structures. See Figure 5.

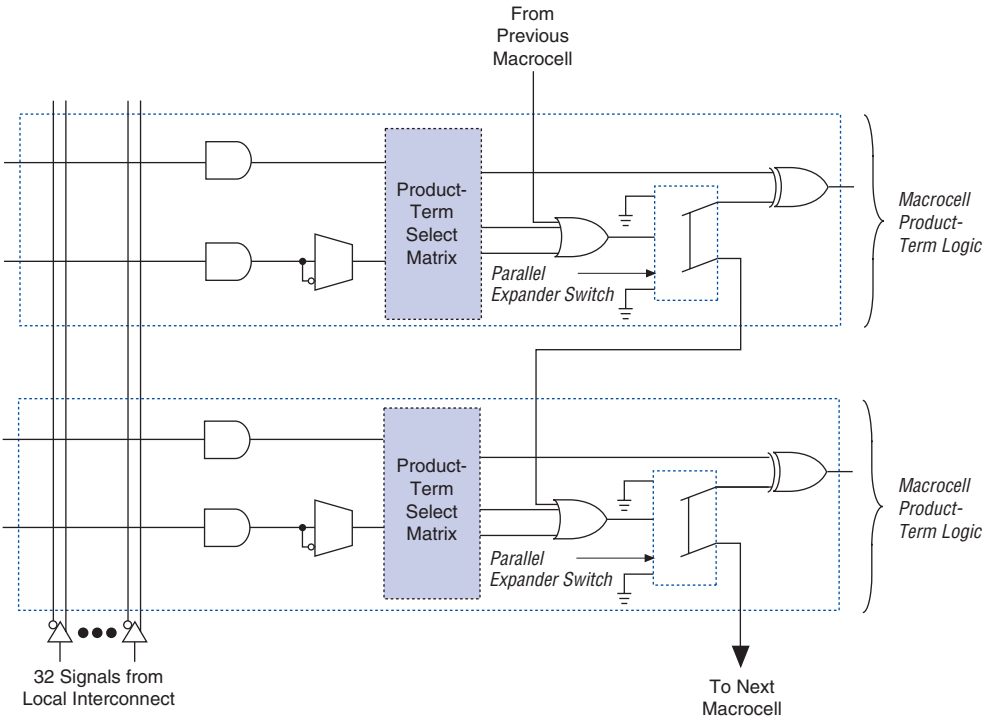
Figure 5. APEX 20KC Logic Element



Each LE's programmable register can be configured for D, T, JK, or SR operation. The register's clock and clear control signals can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the register is bypassed and the output of the LUT drives the outputs of the LE.

Each LE has two outputs that drive the local, MegaLAB, or FastTrack interconnect routing structure. Each output can be driven independently by the LUT's or register's output. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, improves device utilization because the register and the LUT can be used for unrelated functions. The LE can also drive out registered and unregistered versions of the LUT output.

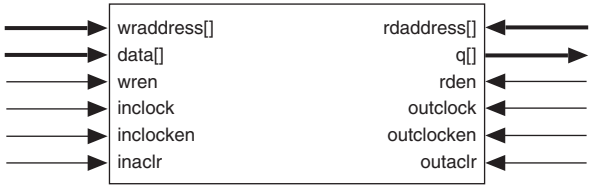
Figure 16. APEX 20KC Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram



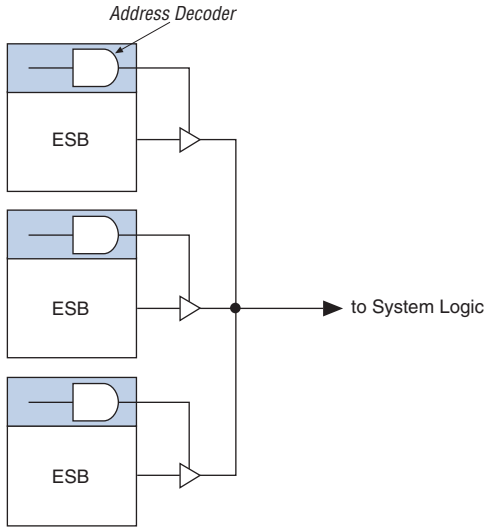
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

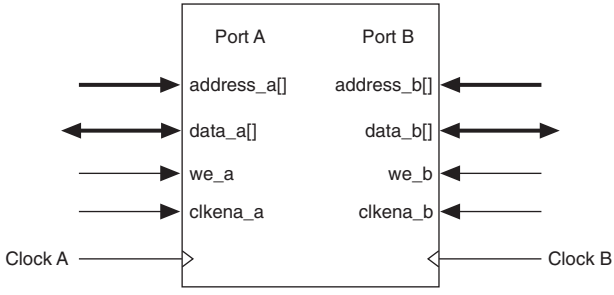
Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two ESBs are used to support two simultaneous reads or writes.

The ESB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 19.

Figure 19. APEX 20KC ESB Implementing Dual-Port RAM



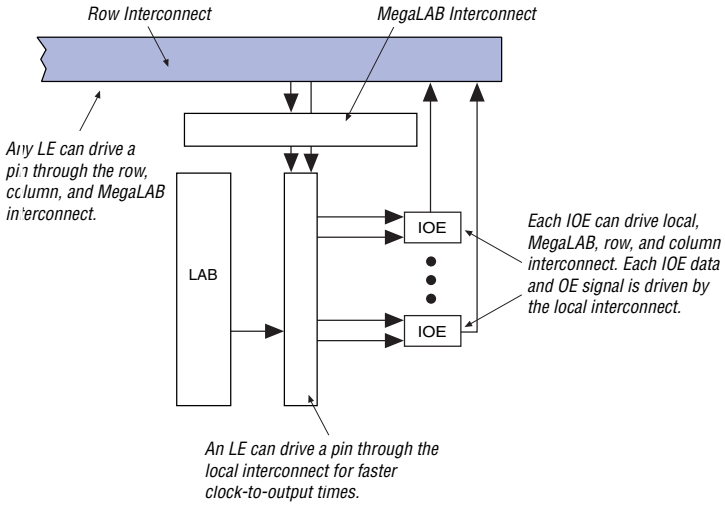
The register in the APEX 20KC IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 25 shows how fast bidirectional I/O pins are implemented in APEX 20KC devices. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Notes to Figure 25:
(1) This programmable delay has four settings: off and three levels of delay.
(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 26 shows how a row IOE connects to the interconnect.

Figure 26. Row IOE Connection to the Interconnect



Advanced I/O Standard Support

APEX 20KC IOEs support the following I/O standards: LVTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.

For more information on I/O standards supported by APEX 20KC devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KC device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL at up to 156 Mbps per channel with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own VCCIO pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate V_{REF} level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K400C and larger APEX 20KC devices support the LVDS interface for data pins (EP20K200C devices support LVDS clock pins, but not data pins). EP20K400C and EP20K600C devices support LVDS for data pins at up to 840 Mbps per channel. EP20K1000C devices support LVDS on 16 channels at up to 750 Mbps.

Each bank can support multiple standards with the same VCCIO for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same VCCIO voltage level. For example, when VCCIO is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used for the LVDS I/O standard, they support all of the other I/O standards. Figure 28 shows the arrangement of the APEX 20KC I/O banks.

Table 20. APEX 20KC Device Capacitance *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 17 through 20:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 4.6 V for input currents less than 100 mA and time periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(7) These values are specified under the APEX 20KC device recommended operating conditions, shown in Table 18 on page 55.
(8) This value is specified for normal device operation. The value may vary during power-up.
(9) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(10) Capacitance is sample-tested only.

Tables 21 through 35 list the DC operating specifications for the supported I/O standards. These tables list minimal specifications only; APEX 20KC devices may exceed these specifications.

Table 21. LVTTL I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –12 mA, V_{CCIO} = 3.0 V *(1)*	2.4		V
V_{OL}	Low-level output voltage	I_{OL} = 12 mA, V_{CCIO} = 3.0 V *(2)*		0.4	V

Table 26. 3.3-V PCI-X Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.35 × V_{CCIO}	V
V_{IPU}	Input pull-up voltage		0.7 × V_{CCIO}			V
I_{IL}	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10.0		10.0	µA
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}			V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
L_{pin}	Pin Inductance				15.0	nH

Table 27. 3.3-V LVDS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.135	3.3	3.465	V
V_{OD}	Differential output voltage	R_L = 100 Ω	250		650	mV
Δ V_{OD}	Change in V_{OD} between high and low	R_L = 100 Ω			50	mV
V_{OS}	Output offset voltage	R_L = 100 Ω	1.125	1.25	1.375	V
Δ V_{OS}	Change in V_{OS} between high and low	R_L = 100 Ω			50	mV
V_{TH}	Differential input threshold	V_{CM} = 1.2 V	–100		100	mV
V_{IN}	Receiver input voltage range		0.0		2.4	V
R_L	Receiver differential input resistor (external to APEX devices)		90	100	110	Ω

Table 30. SSTL-2 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –15.2 mA *(1)*	V_{TT} + 0.76			V
V_{OL}	Low-level output voltage	I_{OL} = 15.2 mA *(2)*			V_{TT} – 0.76	V

Table 31. SSTL-3 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{TT} – 0.6	V

Table 32. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(1)*	V_{TT} + 0.8			V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(2)*			V_{TT} – 0.8	V

Table 33. HSTL Class I I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		1.71	1.8	1.89	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		0.68	0.75	0.90	V
V_{IH}	High-level input voltage		V_{REF} + 0.1		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.1	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{CCIO} – 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			0.4	V

Table 46. EP20K200C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.17		0.20	ns
t_{F5-20}		0.81		0.94		1.12	ns
t_{F20+}		0.98		1.13		1.35	ns

Table 47. EP20K200C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 48. EP20K200C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.23		1.26		1.33		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	3.79	2.00	4.31	2.00	4.70	ns
$t_{INSUPLL}$	0.81		0.92		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.36	0.50	2.62	-	-	ns

Table 57. EP20K600C f_{MAX} ESB Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.30		1.51		1.69	ns
t_{ESBSRC}		2.35		2.49		2.72	ns
t_{ESBAWC}		2.92		3.46		3.86	ns
t_{ESBSWC}		3.05		3.44		3.85	ns
$t_{ESBWASU}$	0.45		0.50		0.54		ns
t_{ESBWAH}	0.44		0.50		0.55		ns
$t_{ESBWDSU}$	0.57		0.63		0.68		ns
t_{ESBWDH}	0.44		0.50		0.55		ns
$t_{ESBRASU}$	1.25		1.43		1.56		ns
t_{ESBRAH}	0.00		0.03		0.11		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	2.01		2.27		2.45		ns
$t_{ESBWADDRSU}$	–0.20		–0.24		–0.28		ns
$t_{ESBRADDRSU}$	0.02		0.00		–0.02		ns
$t_{ESBDATACO1}$		1.09		1.28		1.43	ns
$t_{ESBDATACO2}$		2.10		2.52		2.82	ns
t_{ESBDD}		2.50		2.97		3.32	ns
t_{PD}		1.48		1.78		2.00	ns
$t_{PTERMSU}$	0.58		0.72		0.81		ns
$t_{PTERMCO}$		1.10		1.29		1.45	ns

Table 58. EP20K600C f_{MAX} Routing Delays

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.15		0.16		0.18	ns
t_{F5-20}		0.94		1.05		1.20	ns
t_{F20+}		1.76		1.98		2.23	ns

Table 59. EP20K600C Minimum Pulse Width Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.33		1.66		2.00		ns
t_{CL}	1.33		1.66		2.00		ns
t_{CLRP}	0.20		0.20		0.20		ns
t_{PREP}	0.20		0.20		0.20		ns
t_{ESBCH}	1.33		1.66		2.00		ns
t_{ESBCL}	1.33		1.66		2.00		ns
t_{ESBWP}	1.05		1.28		1.44		ns
t_{ESBRP}	0.87		1.06		1.19		ns

Table 60. EP20K600C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.28		1.40		1.45		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.29	2.00	4.77	2.00	5.11	ns
$t_{INSUPLL}$	0.80		0.91		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.37	0.50	2.63	-	-	ns

Table 69. Selectable I/O Standard Output Delays

Symbol	-7 Speed Grade		-8 Speed Grad		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.00		0.00	ns
1.8 V		1.18		1.41		1.57	ns
PCI		–0.52		–0.53		–0.56	ns
GTL+		–0.18		–0.29		–0.39	ns
SSTL-3 Class I		–0.67		–0.71		–0.75	ns
SSTL-3 Class II		–0.67		–0.71		–0.75	ns
SSTL-2 Class I		–0.67		–0.71		–0.75	ns
SSTL-2 Class II		–0.67		–0.71		–0.75	ns
LVDS		–0.69		–0.70		–0.73	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power estimator on the Altera web site at **http://www.altera.com**.

Configuration & Operation

The APEX 20KC architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.

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